

ABSOLUTE MAXIMUM RATINGS

V_{DD} to GND	–0.5V to 7V
Digital Inputs to GND	–0.5V to ($V_{DD} + 0.5V$)
V_{IOUT} to GND	–0.5V to ($V_{DD} + 0.5V$)
V_{REF} to GND	$\pm 25V$
V_{RFB} to GND	$\pm 25V$
Maximum Junction Temperature	150°C
Operating Temperature Range	–40°C to 85°C
Storage Temperature Range	–65°C to 150°C
Lead Temperature (Soldering, 10 sec)	300°C

PACKAGE/ORDER INFORMATION

TOP VIEW N8 PACKAGE 8-LEAD PDIP S8 PACKAGE 8-LEAD PLASTIC SO $T_{JMAX} = 150^{\circ}C$, $\theta_{JA} = 130^{\circ}C/W$ (N8) $T_{JMAX} = 150^{\circ}C$, $\theta_{JA} = 190^{\circ}C/W$ (S8)		ORDER PART NUMBER
		LTC8043EN8 LTC8043FN8 LTC8043ES8 LTC8043FS8

Consult factory for Military grade parts.

ACCURACY CHARACTERISTICS

 $V_{DD} = 5V$, $V_{REF} = 10V$, $V_{IOUT} = GND = 0V$, $T_A = T_{MIN}$ to T_{MAX} , unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	LTC8043E			LTC8043F			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	
	Resolution		12			12			Bits
INL	Integral Nonlinearity	(Note 1)			± 0.5			± 1	LSB
DNL	Differential Nonlinearity	Guaranteed Monotonic, T_{MIN} to T_{MAX}			± 0.5			± 1	LSB
GE	Gain Error	(Note 2) $T_A = 25^{\circ}C$ T_{MIN} to T_{MAX}			± 1			± 2	LSB
					± 2			± 2	LSB
	Gain Temperature Coefficient ($\Delta Gain/\Delta Temp$)	(Note 3)		1	5		1	5	ppm/ $^{\circ}C$
I_{LKG}	Output Leakage Current	(Note 4) $T_A = 25^{\circ}C$ T_{MIN} to T_{MAX}			± 5			± 5	nA
					± 25			± 25	nA
	Zero-Scale Error	$T_A = 25^{\circ}C$ T_{MIN} to T_{MAX}			± 0.03			± 0.03	LSB
					± 0.15			± 0.15	LSB
PSRR	Power Supply Rejection Ratio	$V_{DD} = 5V \pm 5\%$		± 0.0001	± 0.002		± 0.0001	± 0.002	%/%

ELECTRICAL CHARACTERISTICS

 $V_{DD} = 5V$, $V_{REF} = 10V$, $V_{IOUT} = GND = 0V$, $T_A = T_{MIN}$ to T_{MAX} , unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS		ALL GRADES			UNITS
				MIN	TYP	MAX	
Reference Input							
R _{REF}	V _{REF} Input Resistance	(Note 5)	●	7	11	15	kΩ
AC Performance (Note 3)							
	Output Current Settling Time	(Notes 6, 7)	●		0.25	1	μs
	Multiplying Feedthrough Error	V _{REF} = ±10V, 10kHz Sinewave	●		0.7	1	mV _{P-P}
	Digital-to-Analog Glitch Energy	(Notes 6, 8)	●		2	20	nVSEC
THD	Total Harmonic Distortion	(Note 9)	●		−108	−92	dB
	Output Noise Voltage Density	(Note 10)	●			17	nV/√Hz
Analog Outputs (Note 3)							
C _{OUT}	Output Capacitance	DAC Register Loaded to All 1s	●		60	90	pF
		DAC Register Loaded to All 0s	●		30	60	pF

ELECTRICAL CHARACTERISTICS

$V_{DD} = 5V$, $V_{REF} = 10V$, $V_{IOUT} = GND = 0V$, $T_A = T_{MIN}$ to T_{MAX} , unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	ALL GRADES			UNITS	
			MIN	TYP	MAX		
Digital Inputs							
V _{IH}	Digital Input High Voltage		●	2.4		V	
V _{IL}	Digital Input Low Voltage		●		0.8	V	
I _{IN}	Digital Input Current	V _{IN} = 0V to V _{DD}	●	0.001	±1	μA	
C _{IN}	Digital Input Capacitance	V _{IN} = 0V,(Note 3)	●		8	pF	
Timing Characteristics (Note 3)							
t _{DS}	Serial Input to Clock Setup Time		●	30	–5	ns	
t _{DH}	Serial Input to Clock Hold Time		●	60	25	ns	
t _{SRI}	Serial Input Data Pulse Width		●	80		ns	
t _{CH}	Clock Pulse Width High		●	80		ns	
t _{CL}	Clock Pulse Width Low		●	80		ns	
t _{LD}	Load Pulse Width		●	140		ns	
t _{ASB}	LSB Clocked into Input Register to Load DAC Register Time		●	0		ns	
Power Supply							
V _{DD}	Supply Voltage		●	4.75	5	5.25	V
I _{DD}	Supply Current	Digital Inputs = 0V or V _{DD}	●		100		μA
		Digital Inputs = V _{IH} or V _{IN}	●		500		μA

The ● denotes specifications which apply over the full operating temperature range.

Note 1: $\pm 0.5LSB = \pm 0.012\%$ of full scale.

Note 2: Using internal feedback resistor.

Note 3: Guaranteed by design, not subject to test.

Note 4: I_{OUT} with DAC register loaded with all 0s.

Note 5: Typical temperature coefficient is 100ppm/°C.

Note 6: I_{OUT} load = 100Ω in parallel with 13pF.

Note 7: To 0.01% for a full-scale change, measured from falling edge of $\overline{LD}$.

Note 8: $V_{REF} = 0V$. DAC register contents changed from all 0s to all 1s or from all 1s to all 0s.

Note 9: $V_{REF} = 6V_{RMS}$ at 1kHz. DAC register loaded with all 1s.

Note 10: 10Hz to 100kHz between R_{FB} and I_{OUT} . Calculation from $e_n = \sqrt{4KTRB}$ where: K = Boltzmann constant (J/K°); R = resistance (Ω); T = resistor temperature (°K); B = bandwidth (Hz).

BLOCK DIAGRAM



